

Silicon Phototransistor in SMT Plastic Package

OP580

- Wide Acceptance Angle
- Fast Response Time
- Plastic Leadless Chip Carrier (PLCC)

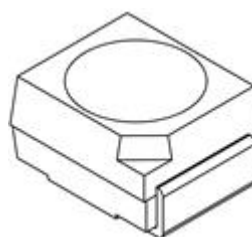
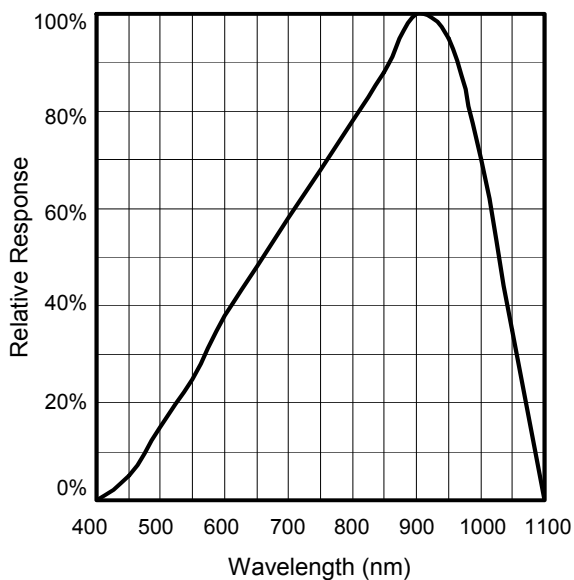


The OP580 is an NPN silicon phototransistor mounted in a miniature SMT package. The device has a flat window lens which enables a wide acceptance angle. This device is packaged in a plastic leadless chip carrier that is compatible with most automated mounting equipment. The OP580 is mechanically and spectrally matched to the OP280 infrared LED.

Applications

- Non-Contact Position Sensing
- Datum detection
- Machine automation
- Optical encoders

Relative Response vs. Wavelength



OP580



RoHS

Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Storage Temperature Range	-40° C to +85° C
Operating Temperature Range	-25° C to +85° C
Lead Soldering Temperature	260° C ⁽¹⁾
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Collector Current	20 mA
Power Dissipation	75 mW ⁽²⁾

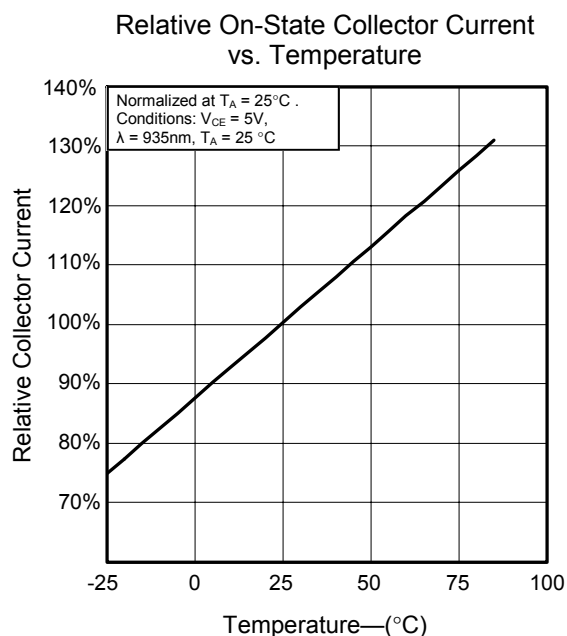
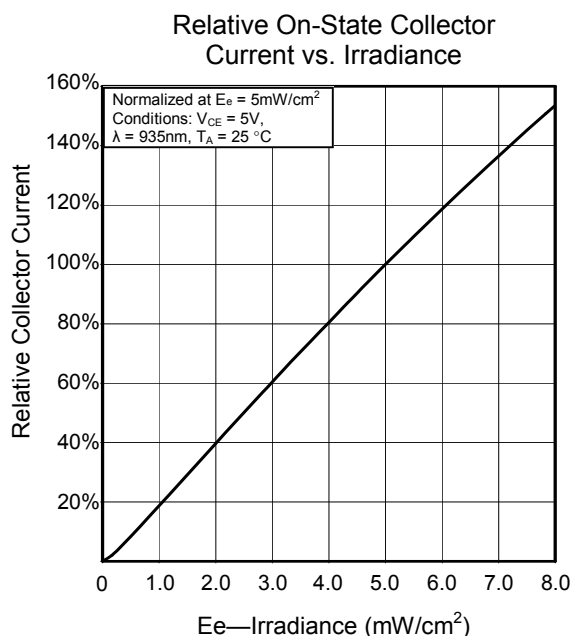
Notes:

- Solder time less than 5 seconds at temperature extreme.
- De-rate linearly at 2.17 mW/° C above 25° C.

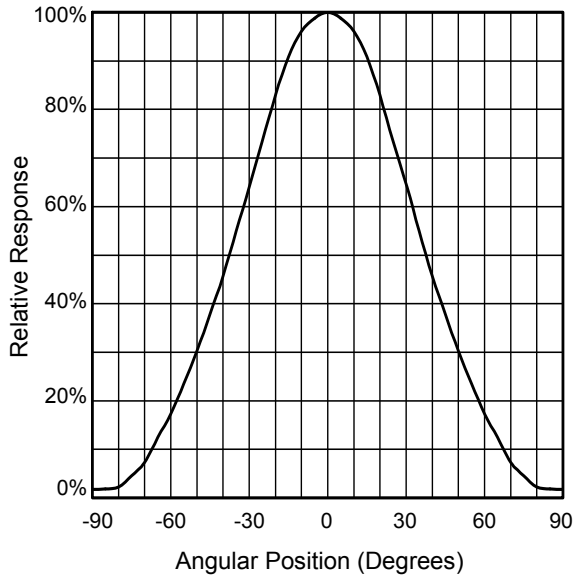
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
$I_{C(ON)}$	On-State Collector Current	1.0			mA	$V_{CE} = 5.0\text{V}$, $E_e = 5.0\text{mW}/\text{cm}^2$ ⁽³⁾
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage			0.4	V	$I_C = 100\mu\text{A}$, $E_e = 2.0\text{mW}/\text{cm}^2$ ⁽³⁾
I_{CEO}	Collector-Emitter Dark Current			100	nA	$V_{CE} = 5.0\text{V}$, $E_e = 0$ ⁽⁴⁾
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30			V	$I_C = 100\mu\text{A}$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5			V	$I_E = 100\mu\text{A}$
t_r, t_f	Rise and Fall Times		15		μs	$I_C = 1\text{mA}$, $R_L = 1\text{K}\Omega$

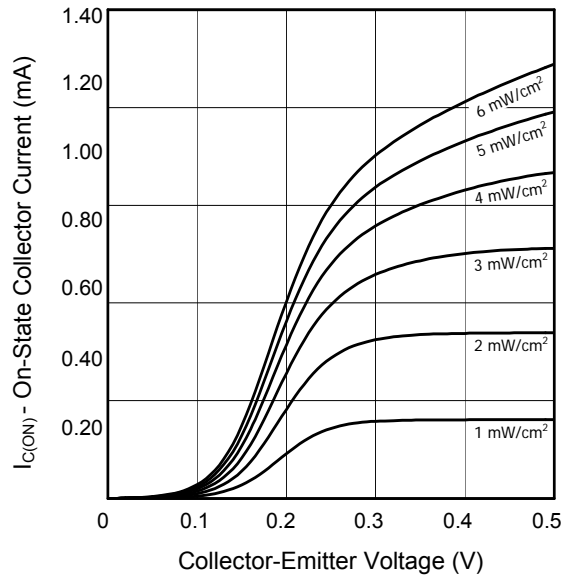
- Light source is an unfiltered GaAs LED with a peak emission wavelength of 935nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the phototransistor being tested.
- To Calculate typical collector dark current in μA , use the formula $I_{CEO} = 10^{(0.04 T_A - 3/4)}$ where T_A is the ambient temperature in ° C.



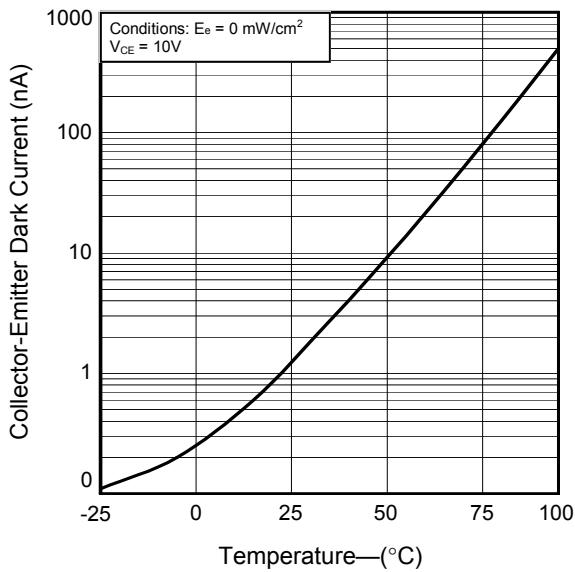
Relative Response vs. Angular Position



Relative On-State Collector Current vs. Collector-Emitter Voltage

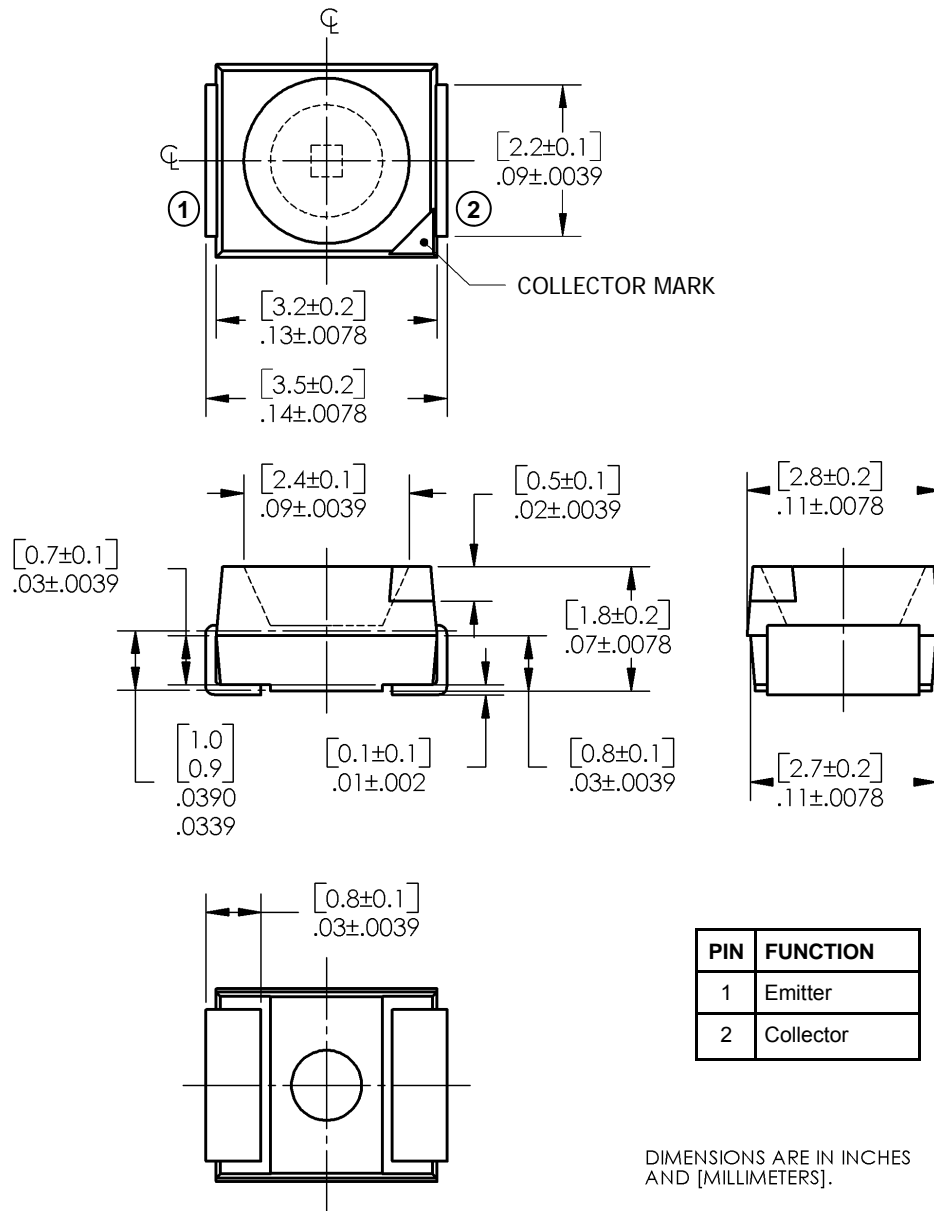


Collector-Emitter Dark Current vs. Temperature

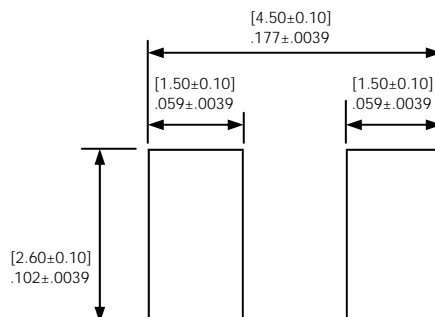


SMT Silicon Phototransistor

OP580



RECOMMENDED SOLDER PADS



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